

**Amendments to the Specification:**

Please replace the paragraph beginning at page 1, line 2, with the following amended paragraph:

The present invention is related to, and claims priority from, United States Provisional Patent Application Ser. No. 60/500,126 filed September 4, 2003 for: "0.6V 205MHz 19.5nsec TRC 16Mb Embedded DRAM" the disclosure of which is herein specifically incorporated in its entirety by this reference. The present invention is further related to the subject matter disclosed in United States Patent Applications Serial No. ~~[UMI-355]~~ 10/776,103 entitled: "Sense Amplifier Power-Gating Technique for Integrated Circuit Memory Devices and Those Devices Incorporating Embedded Dynamic Random Access Memory (DRAM)" and ~~[UMI-359]~~ 10/776,054 entitled "Column Read Amplifier Power-Gating Technique for Integrated Circuit Memory Devices and Those Devices Incorporating Embedded Dynamic Random Access Memory (DRAM)", the disclosures of which are herein specifically incorporated by this reference in its entirety.